L Number	Hits	Search Text	DB	Time stamp
4	633	(359/223).CCLS.	USPAT;	2003/07/30
			US-PGPUB;	08:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	304	(359/298).CCLS.	USPAT;	2003/07/30
		,	US-PGPUB;	08:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	581	(359/838). <i>CC</i> L5.	USPAT;	2003/07/30
	551	(407/000).0000.	US-PGPUB;	08:23
			EPO; JPO;	00.23
			DERWENT;	
			IBM_TDB	
7	88	(205/116).CCLS.	USPAT;	2003/07/30
′	66	(203/110).0003.	US-PGPUB;	08:27
				08:27
			EPO; JPO;	
			DERWENT;	
	400		IBM_TDB	2000 (27 (20
8	422	((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
		silicon) and (internal with (mirror or reflect\$))	US-PGPUB;	09:34
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
9	71	(((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
		silicon) and (internal with (mirror or reflect\$))) and	US-PGPUB;	08:31
		anisotrop\$	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	5	((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
		silicon) and (internal\$2 with (mirror or reflect\$) with	US-PGPUB;	09:02
		etch\$4)	EPO; JPO;	
			DERWENT;	
			IBW_TDB	
11	1	((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
:		silicon) and (atom\$6 with flat with (mirror or	US-PGPUB;	09:04
		reflect\$) with etch\$4)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	6	((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
		silicon) and (atom\$6 with flat with (mirror or	US-PGPUB;	09:07
		reflect\$))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	0	((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
		silicon) and (atom\$6 with flat with anisotrop\$)	US-PGPUB;	09:08
			EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	

		11. 11. 11. 11. 11. 11. 11. 11.	LICEAT	2002/07/22
14	2	silicon same (atom\$6 with flat with anisotrop\$)	USPAT;	2003/07/30
			US-PGPUB;	09:10
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
15	5	silicon same (atom\$6 with flat) same anisotrop\$	USPAT;	2003/07/30
			US-PGPUB;	09:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	512	((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
		silicon) and ((internal or bur\$3) with (mirror or	US-PGPUB;	09:13
		reflect\$))	EPO; JPO;	
		1010014))	DERWENT;	
			IBM_TDB	
17	356	((/hlk an (ainala naon3 am;atal¢) an hamacan¢) naon3	USPAT;	2003/07/30
17	336	(((bulk or (single near3 crystal\$) or homogen\$) near3	1	
		silicon) and ((internal or bur\$3) with (mirror or	US-PGPUB;	09:14
		reflect\$))) and etch\$4	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
18	69	(((bulk or (single near3 crystal\$) or homogen\$) near3	USPAT;	2003/07/30
		silicon) and ((internal or bur\$3) with (mirror or	US-PGPUB;	09:14
		reflect\$))) and (etch\$4 with plane)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	166	((bulk or crystal\$ or homogen\$) near3 silicon) and	USPAT;	2003/07/30
		(internal with (mirror or reflect\$ or deflect\$)) and	US-PGPUB;	10:15
		anisotrop\$	EPO; JPO;	
		, .	DERWENT;	
			IBM_TDB	
21	324	((bulk or crystal\$ or homogen\$) near3 silicon) and	USPAT;	2003/07/30
		(integra\$ with (mirror or reflect\$ or deflect\$)) and	US-PGPUB;	11:13
		anisotrop\$	EPO; JPO;	11.10
		amson opp	DERWENT;	
			IBM_TDB	
22	7	 ("4182544" "4657339" "4669817" "4674828"	USPAT	2002/07/20
22	'	· · · · · · · · · · · · · · · · · · ·	USPAT	2003/07/30
22	/42	"4675521" "4684208" "4705349").PN.	HEDAT	11:04
23	642	silicon and (integra\$ with (mirror or reflect\$ or	USPAT;	2003/07/30
		deflect\$)) and (anisotrop\$ with etch\$3)	US-PGPUB;	11:16
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
24	182	(integra\$ with (mirror or reflect\$ or deflect\$)) and	USPAT;	2003/07/30
		(silicon with anisotrop\$ with etch\$3) and (hole or	US-PGPUB;	11:56
		bore or passage)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
25	84	(silicon with (mirror or reflect\$ or deflect\$) with	USPAT;	2003/07/30
		(micromachin\$ or micro?machin\$)) and (anisotrop\$	US-PGPUB;	11:58
		with etch\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	L		100	l

	35	() . A(2 () . () A () . () A () . () A	LICDAT	2002/07/20
26	35	(atom\$6 near3 (smooth\$4 or flat\$4)) with etch\$4	USPAT;	2003/07/30
		with silicon	US-PGPUB;	12:25
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
27	256	(atom\$6 near3 (smooth\$4 or flat\$4)) and (mirror or	USPAT;	2003/07/30
		reflect\$ or deflect\$) and etch\$4 and silicon	US-PGPUB;	12:26
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	35	((atom\$6 near3 (smooth\$4 or flat\$4)) same (mirror	USPAT;	2003/07/30
		or reflect\$ or deflect\$)) and etch\$4 and silicon	US-PGPUB;	12:31
		, , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
29	52	(atom\$6 near3 (smooth\$4 or flat\$4)) and (mirror or	USPAT;	2003/07/30
-/		reflect\$ or deflect\$) and (anisotrop\$ with etch\$4)	US-PGPUB;	12:32
		and silicon	EPO; JPO;	25.05
1		and sincon	DERWENT;	
	2	(II.C.O.O.G.1.2.Q.II.). D. I.	IBM_TDB	2002/00/17
-		("6008128").PN.	USPAT;	2002/09/17
			US-PGPUB;	09:09
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	576	(359/223). <i>CC</i> LS.	USPAT;	2003/03/07
			US-PGPUB;	17:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	255	(359/298). <i>CC</i> LS.	USPAT;	2003/03/07
			US-PGPUB;	17:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	505	(359/838).CCLS.	USPAT;	2003/03/07
]		US-PGPUB;	17:14
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	88	(205/116).CCLS.	USPAT;	2003/03/07
			US-PGPUB;	17:15
			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
_	135	((359/223).CCL5.) and silicon\$	USPAT;	2002/09/17
		,	US-PGPUB;	09:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
L		<u> </u>		

			1	I 2000 100 110
-	85	((359/298).CCLS.) and silicon\$	USPAT;	2002/09/17
1]		US-PGPUB;	10:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	66	((359/838).CCL5.) and silicon\$	USPAT;	2002/09/17
	·		US-PGPUB;	10:30
			EPO; JPO;	
			DERWENT;	
i			IBM_TDB	
_	8	((205/116).CCL5.) and silicon\$	USPAT;	2002/09/17
			US-PGPUB;	10:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	421	silicon and mirror and bulk and monolith\$ and	USPAT;	2002/09/17
-	421	· ·	US-PGPUB;	10:43
		crystal\$4	1	10.43
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	46	(silicon and mirror and bulk and monolith\$ and	USPAT;	2002/09/17
		crystal\$4) and inlet and outlet	US-PGPUB;	10:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31	silicon and mirror and bulk and monolith\$ and	USPAT;	2002/09/17
		(crystal\$4 adj plane)	US-PGPUB;	10:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	89	(single adj crystal adj silicon) and mirror and	USPAT;	2003/07/30
		(crystal\$4 adj plane)	US-PGPUB;	08:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	692	(single adj crystal adj silicon) and mirror and plane	USPAT;	2002/09/17
		and etch\$3	US-PGPUB;	11:43
		and Orongo	EPO; JPO;	*4.70
			DERWENT;	
	300	الماسماء مطالع المعالمة المطالعة المطال	IBM_TDB	2002/00/17
-	309	((single adj crystal adj silicon) and mirror and plane	USPAT;	2002/09/17
		and etch\$3) and anisotrop\$	US-PGPUB;	11:09
			EPO; JPO;	
			DERWENT;	_
			IBM_TDB	
-	101	(((single adj crystal adj silicon) and mirror and plane	USPAT;	2002/09/17 11:10
		and etch\$3) and anisotrop\$) and fiber and optic\$4	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	121	(single and crystal and silicon) and mirror and plane	USPAT;	2002/09/17 14:11
		and etch\$3 and anisotrop\$ and fiber and optic\$4 and	US-PGPUB;	
		internal\$2	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	256	singl and crystal\$4 and silicon and mirror and	USPAT;	2002/09/17
_		etch\$3 and stripe and intersect\$4	US-PGPUB;	14:25
		erchips and stripe and intersection	EPO; JPO;	14.65
			DERWENT;	
			IBM_TDB	
	118	(single and crystal\$4 and silicon and mirror and	USPAT;	2002/09/17
-	110	etch\$3 and stripe and intersect\$4) and internal	US-PGPUB;	11:58
		erchips and stripe and intersectip4) and internal	EPO; JPO;	11.56
			DERWENT;	
			1	
	272	Con 1 and 1864 and 18 November 1981	IBM_TDB	2002/00/17
-	373	(single near crystal\$4 near silicon) with mirror	USPAT;	2002/09/17
			US-PGPUB;	12:05
			EPO; JPO;	i .
			DERWENT;	
			IBM_TDB	
-	39	((single near crystal\$4 near silicon) with mirror) and	USPAT;	2002/09/17
		(fiber near optic\$4)	US-PGPUB;	12:06
			EPO; JPO;	
			DERWENT;	
			IBW_LDB	
-	3645	digital and mirror and device and silicon and	USPAT;	2002/09/17
		crystal\$4	US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	168	(digital and mirror and device and silicon and	USPAT;	2002/09/17
		crystal\$4) and bulk and monolith\$	US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	341	silicon and mirror and etch\$3 and stripe and	USPAT;	2002/09/17
		intersect\$4	US-PGPUB;	14:36
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	2259	silicon and mirror and pattern\$3 and anisotrop\$	USPAT;	2002/09/17
			US-PGPUB;	14:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	403	(single adj crystal\$4 adj silicon) and mirror and	USPAT;	2002/09/17
		pattern\$3 and anisotrop\$	US-PGPUB;	15:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

		/	LICDAT	2002/00/17
-	0	(bulk with (single adj crystal\$4 adj silicon)) and	USPAT;	2002/09/17
		(mirror near pattern\$3)	US-PGPUB;	15:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	20	silicon and (mirror near patt rn\$3) and (anisotrop\$	USPAT;	2002/09/17
		near etch\$3)	US-PGPUB;	15:34
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	16	silicon and ((mirror near pattern\$3) with array\$)	USPAT;	2002/09/17
			US-PGPUB;	15:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2585	(mirror with array\$) and silicon	USPAT;	2002/09/17
		,	US-PGPUB;	16:16
			EPO; JPO;	
	-		DERWENT;	
			IBM_TDB	
_	9	(mirror with array\$) and (bulk with single with	USPAT;	2002/09/17
		crystal\$4 with silicon)	US-PGPUB;	15:43
		crystalp+ with silicony	EPO; JPO;	15.45
			DERWENT;	,
				•
	2	((n) in a notation of and all and a notation of and	IBM_TDB	2002/00/17
_	_	((mirror with array\$) and silicon) and anisotrop\$ and	USPAT;	2002/09/17
		(bulk near crystal\$4)	US-PGPUB;	15:44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	monolithic adj bulk adj crystal adj silicon	USPAT;	2002/09/17
			US-PGPUB;	16:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	monolithic with bulk with crystal with silicon	USPAT;	2002/09/17
			US-PGPUB;	16:17
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
-	1586	monolithic and bulk and crystal and silicon	USPAT;	2002/09/17
			US-PGPUB;	16:18
1]		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	25	(monolithic and bulk and crystal and silicon) and	USPAT;	2002/09/17
		(crystalline near plane)	US-PGPUB;	16:19
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

_	362	(monolithic and bulk and crystal and silicon) and	USPAT;	2002/09/17
		(crystalline and plane)	US-PGPUB;	16:20
		(crystamic and plane)	EPO; JPO;	10.20
			DERWENT;	
			IBM_TDB	
	4	((monolithic and bulk and crystal and silicon) and	USPAT;	2002/09/17
-		(crystalline and plane)) and (micro?mirror or (micro	US-PGPUB;	16:20
		1 - 1	EPO; JPO;	10.20
		adj mirror))	DERWENT;	
	109	((manalish) a and bulk and amaskal and siliaan) and	IBM_TDB USPAT;	2002/00/17
-	109	((monolithic and bulk and crystal and silicon) and	1	2002/09/17
		(crystalline and plane)) and mirror	US-PGPUB;	16:41
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	4	silicon near mirror near array	USPAT;	2002/09/17
			US-PGPUB;	16:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1415	digital near (micromirror or micro?mirror or (micro	USPAT;	2002/09/17
		adj mirror)) near device	US-PGPUB;	16:43
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	350	(digital near (micromirror or micro?mirror or (micro	USPAT;	2002/09/17
		adj mirror)) near device) and silicon	US-PGPUB;	17:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	16	(digital near (micromirror or micro?mirror or (micro	USPAT;	2002/09/17
		adj mirror)) near device) and (single adj crystal adj	US-PGPUB;	17:14
		silicon)	EPO; JPO;	
	!		DERWENT;	
			IBM_TDB	
-	3991	(mirror or reflect\$) and (single adj crystal adj	USPAT;	2002/09/17
		silicon)	US-PGPUB;	17:16
		<u> </u>	EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
-	240	((mirror or reflect\$) and (single adj crystal adj	USPAT;	2002/09/17
		silicon)) and bulk and monolith\$	US-PGPUB;	17:42
		Sincerny and Bon and Mononing	EPO; JPO;	17.12
			DERWENT;	
			IBM_TDB	
_	148	anisotrop\$ with silicon with array with etch\$4	USPAT;	2002/09/17
	140	amoun opp with sincon with allay with elempt	US-PGPUB;	17:43
			EPO; JPO;	17.73
			DERWENT;	
	1		1	
			IBM_TDB	1

	226	(anisotrop\$ with silicon with process\$) and (mirror or	USPAT;	2002/09/17
	220	refl ctor)	US-PGPUB;	18:38
			EPO; JPO;	10.30
			DERWENT;	
			IBM_TDB	
	25	silicon and mirror and passage and (crystalline adj	USPAT;	2002/09/17
-	25	, , ,	US-PGPUB;	18:42
		plane)	EPO; JPO;	10.72
			DERWENT;	
			IBM_TDB	
	42	Constitution and built and amended and efficient and	USPAT;	2002/09/17
-	42	(monolithic and bulk and crystal and silicon) and		
		(mirror or reflector) and crystalline and plane and	US-PGPUB;	18:44
		intersect\$4	EPO; JPO;	
			DERWENT;	
		(250 (202) 66) 6	IBM_TDB	2002/07/20
-	606	(359/223).CCLS.	USPAT;	2003/07/30
			US-PGPUB;	08:10
] .		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	290	(359/298).CCLS.	USPAT;	2003/07/30
			US-PGPUB;	08:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	553	(359/838). <i>CC</i> LS.	USPAT;	2003/07/30
			US-PGPUB;	08:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	88	(205/116).CCLS.	USPAT;	2003/07/30
			US-PGPUB;	08:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	42	((359/223).CCLS.) and (mirror or reflector) and	USPAT;	2003/03/07
		anisotrop\$	US-PGPUB;	17:28
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
-	23	((359/298).CCL5.) and (mirror or reflector) and	USPAT;	2003/03/07
		anisotrop\$	US-PGPUB;	17:52
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
-	15	((359/838).CCL5.) and (mirror or reflector) and	USPAT;	2003/03/07
		anisotrop\$	US-PGPUB;	17:54
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	

-	1	((205/116).CCLS.) and (mirror or reflector) and	USPAT;	2003/03/07
		anisotrop\$	US-PGPUB;	17:56
			EPO; JPO;	
	ļ		DERWENT;	
			IBM_TDB	
_	244	silicon and ((mirror or refl ctor) with anisotrop\$)	USPAT;	2003/03/10
			US-PGPUB;	08:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2	westra.in. and silicon and anisotrop\$	USPAT;	2003/03/10
		, .	US-PGPUB;	08:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	101	westra.in.	USPAT;	2003/03/10
			US-PGPUB;	08:21
			EPO; JPO;	
<u> </u>	1		DERWENT;	
			IBM_TDB	